2SC3403

Silicon PNP Triple-Diffused Planar Type

High Breakdown Voltage, High Speed Switching

■ Features

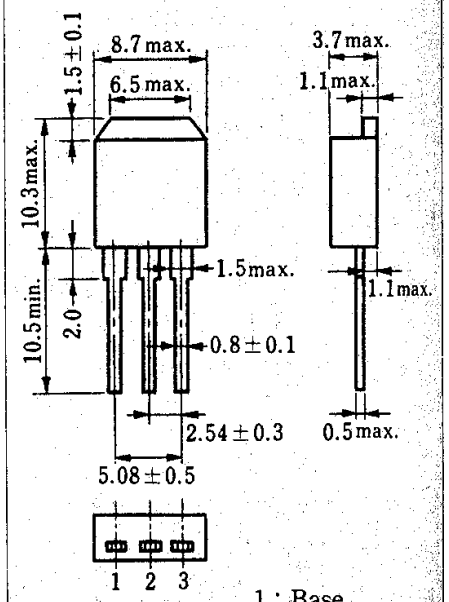
- High speed switching
- Low collector-emitter saturation voltage ($V_{CE\ (sat)}$)
- "N Type" package configuration with a cooling fin for direct soldering on PC borad of a small-size electronic equipment

■ Absolute Maximum Ratings (Tc=25°C)

Item		Symbol	Value	Unit
Collector-base voltage		V_{CBO}	500	V
Collector-emitter voltage		V_{CEO}	400	V
Emitter-base voltage		V_{EBO}	7	V
Peak collector current		I_{CP}	4	A
Collector current		I_C	2	A
Collector power dissipation	Tc=25℃	P_C	25	W
	Ta=25℃		1.3	
Junction temperature		T_j	150	℃
Storage temperature		T_{stg}	−55~+150	℃

■ Package Dimensions

Unit : mm



1 : Base
2 : Collector
3 : Emitter
N Type Package

*Surface-mount type is also available.
(Refer to p.82.)

■ Electrical Characteristics (Tc=25°C)

Item	Symbol	Condition	min.	typ.	max.	Unit
Collector cutoff current	I_{CBO}	V_{CB}=500 V, I_E=0			100	μA
Emitter cutoff current	I_{EBO}	V_{EB}=5 V, I_C=0			100	μA
Collector-emitter voltage	$V_{CEO(sus)}$	I_C=0.2 A, L=25 mH	400			V
DC current gain	h_{FE1}	V_{CE}=5 V, I_C=0.1 A	15			
	h_{FE2}	V_{CE}=5 V, I_C=1 A	8			
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=1 A, I_B=0.2 A			1	V
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C=1 A, I_B=0.2 A			1.5	V
Transition frequency	f_T	V_{CE}=10V, I_C=0.2A, f=1MHz	8			MHz
Turn-on time	t_{on}	I_C=1 A, I_{B1}=0.2 A, I_{B2}=−0.2 A, V_{CC}=150V			1	μs
Storage time	t_{stg}				3	μs
Fall time	t_f				1	μs

* $V_{CEO\ (sus)}$ Test method

